

Title (en)

INTEGRATED CIRCUIT AND METHOD FOR MAKING SAME

Title (de)

INTEGRIERTER SCHALTKEIS UND HERSTELLUNGSVERFAHREN

Title (fr)

CIRCUIT INTEGRE ET PROCEDE DE FABRICATION

Publication

EP 1350267 A1 20031008 (FR)

Application

EP 02710090 A 20020109

Priority

- FR 0200054 W 20020109
- FR 0100419 A 20010112

Abstract (en)

[origin: WO02056370A1] Sn one particular embodiment, the integrated circuit comprises a load storing semiconductor device comprising at least a control transistor T and a storage capacitor TRC. The device comprises a substrate including a lower region containing at least a buried capacitive trench TRC forming said storage capacitor, a casing CS located above said lower region of the substrate. The control transistor T is produced in and on the casing and said capacitive trench is located beneath the transistor and is in contact with the casing.

[origin: WO02056370A1] In one particular embodiment, the integrated circuit comprises a load storing semiconductor device comprising at least a control transistor T and a storage capacitor TRC. The device comprises a substrate including a lower region containing at least a buried capacitive trench TRC forming said storage capacitor, a casing CS located above said lower region of the substrate. The control transistor T is produced in and on the casing and said capacitive trench is located beneath the transistor and is in contact with the casing.

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IPC 8 full level

H01L 21/8242 (2006.01); **H01L 27/108** (2006.01)

CPC (source: EP US)

H01L 27/14683 (2013.01 - EP US); **H01L 29/808** (2013.01 - EP US); **H10B 12/038** (2023.02 - EP US); **H10B 12/05** (2023.02 - EP US); **H10B 12/373** (2023.02 - EP US)

Citation (search report)

See references of WO 02056370A1

Designated contracting state (EPC)

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DOCDB simple family (publication)

WO 02056370 A1 20020718; **WO 02056370 A8 20020808**; EP 1350267 A1 20031008; FR 2819632 A1 20020719; FR 2819632 B1 20030926; US 2004113193 A1 20040617; US 2007015326 A1 20070118; US 7115933 B2 20061003; US 7470585 B2 20081230

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